

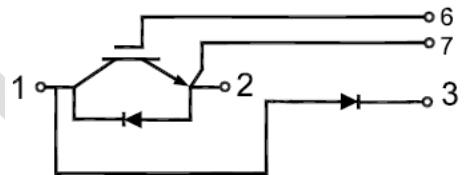
# GT300CU120T2VH-M

## IGBT Module

Preliminary Data

### Features:

- Field Stop Trench Gate IGBT
- Short Circuit Rated > 10 $\mu$ s
- Low Saturation Voltage
- Low Switching Loss
- 100% RBSOA Tested(2 $\times$ I<sub>c</sub>)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



### Applications:

- Welding
- HEV Inverter
- Industrial Motor Drives
- UPS

### IGBT, Brake-Chopper

Maximum Rated Values of IGBT(T<sub>C</sub>=25 $^{\circ}$ C unless otherwise specified)

V <sub>CES</sub>	Collector-Emitter Blocking Voltage		1200	V
V <sub>GES</sub>	Gate-Emitter Voltage		$\pm$ 20	V
I <sub>C</sub>	Continuous Collector Current	T <sub>C</sub> =100 $^{\circ}$ C	300	A
		T <sub>C</sub> =25 $^{\circ}$ C	580	A
I <sub>CM</sub>	Repetitive Peak Collector Current	T <sub>J</sub> =175 $^{\circ}$ C	600	A
t <sub>SC</sub>	Short Circuit Withstand Time		>10	$\mu$ s
P <sub>D</sub>	Maximum Power Dissipation per IGBT	T <sub>C</sub> =25 $^{\circ}$ C T <sub>Jmax</sub> =175 $^{\circ}$ C	1975	W

## Electrical Characteristics of IGBT ( $T_C=25^\circ\text{C}$ unless otherwise specified)

### Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 4\text{mA}, V_{CE} = V_{GE}$	5.0	5.6	6.6	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 300\text{A}, V_{GE} = 15\text{V}$	$T_J=25^\circ\text{C}$	1.70	1.90	V
			$T_J=125^\circ\text{C}$	1.90		V
			$T_J=150^\circ\text{C}$	2.00		V
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_J = 25^\circ\text{C}$			1	mA
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}, T_J = 25^\circ\text{C}$			400	nA
$C_{ies}$	Input Capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		19.71		nF
$C_{oes}$	Output Capacitance			1.68		nF
$C_{res}$	Reverse Transfer Capacitance			1.10		nF

### Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 600\text{V}, I_C = 300\text{A}, R_{Gon} = 2\Omega, V_{GE} = \pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	0.39		$\mu\text{s}$
			$T_J=125^\circ\text{C}$	0.40		
			$T_J=150^\circ\text{C}$	0.40		
$t_r$	Rise Time		$T_J=25^\circ\text{C}$	0.13		$\mu\text{s}$
			$T_J=125^\circ\text{C}$	0.13		
			$T_J=150^\circ\text{C}$	0.13		
$t_{d(off)}$	Turn-off Delay Time		$T_J=25^\circ\text{C}$	0.39		$\mu\text{s}$
			$T_J=125^\circ\text{C}$	0.42		
			$T_J=150^\circ\text{C}$	0.42		
$t_f$	Fall Time	$T_J=25^\circ\text{C}$	0.13		$\mu\text{s}$	
		$T_J=125^\circ\text{C}$	0.19			
		$T_J=150^\circ\text{C}$	0.21			
$E_{on}$	Turn-on Switching Loss	$V_{CC} = 600\text{V}, I_C = 300\text{A}, R_{Gon} = 2\Omega, V_{GE} = \pm 15\text{V},$ $di/dt=1880\text{A}/\mu\text{s} (T_J=150^\circ\text{C})$ Inductive Load	$T_J=25^\circ\text{C}$	20.6		mJ
			$T_J=125^\circ\text{C}$	27.3		
			$T_J=150^\circ\text{C}$	29.7		

E <sub>off</sub>	Turn-off Switching Loss	V <sub>CC</sub> = 600V, I <sub>C</sub> = 300A, R <sub>Goff</sub> = 2Ω, V <sub>GE</sub> = ±15V, du/dt=3300V/μs ( T <sub>J</sub> =150°C) Inductive Load	T <sub>J</sub> =25°C	26.7	mJ
			T <sub>J</sub> =125°C	35.6	
			T <sub>J</sub> =150°C	38.3	
Q <sub>g</sub>	Total Gate Charge	V <sub>GE</sub> =+15V...-15V	T <sub>J</sub> =25°C	1.56	μC
R <sub>g internal</sub>	Internal Gate Resistance		T <sub>J</sub> =25°C	2.5	Ω
RBSOA	I <sub>C</sub> =600A, V <sub>CC</sub> =1050V, V <sub>p</sub> =1200V, R <sub>Goff</sub> = 2Ω, V <sub>GE</sub> =+15V to 0V, T <sub>J</sub> =150°C			Trapezoid	
I <sub>SC</sub>	SC Data	V <sub>CC</sub> =600V, V <sub>GE</sub> =±15V, R <sub>Gon</sub> =2ohm, R <sub>Goff</sub> =2ohm, tp=10us, T <sub>J</sub> =125°C, Inductive Load		1594	A
R <sub>θJC</sub>	IGBT Thermal Resistance: Junction-To-Case(per leg)			0.076	°C/W

### Diode, Reverse

#### Maximum Rated Values of Diode (T<sub>C</sub>=25°C unless otherwise specified)

V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	V
I <sub>F</sub>	Diode Continuous Forward Current	200	A
I <sub>FM</sub>	Diode Maximum Forward Current	400	A

#### Electrical Characteristics of Diode (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
V <sub>FM</sub>	Forward Voltage	I <sub>F</sub> =200A	T <sub>J</sub> =25°C	1.60		V
			T <sub>J</sub> =125°C	1.70		
			T <sub>J</sub> =150°C	1.70		
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =200A, -di <sub>F</sub> /dt =1855A/μs(T <sub>J</sub> =150°C), V <sub>R</sub> = 600V, V <sub>GE</sub> = -15V	T <sub>J</sub> =25°C	0.32		μs
			T <sub>J</sub> =125°C	0.53		
			T <sub>J</sub> =150°C	0.56		
I <sub>rr</sub>	Peak Reverse Recovery Current	I <sub>F</sub> =200A, -di <sub>F</sub> /dt =1855A/μs(T <sub>J</sub> =150°C), V <sub>R</sub> = 600V, V <sub>GE</sub> = -15V	T <sub>J</sub> =25°C	128		A
			T <sub>J</sub> =125°C	144		
			T <sub>J</sub> =150°C	150		

Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> =200A, -diF/dt =1855A/μs(T <sub>J</sub> =150°C), V <sub>R</sub> = 600V, V <sub>GE</sub> = -15V	T <sub>J</sub> =25°C	20.7	μC
			T <sub>J</sub> =125°C	34.5	
			T <sub>J</sub> =150°C	38.8	
E <sub>rec</sub>	Reverse Recovery Energy		T <sub>J</sub> =25°C	8.5	mJ
			T <sub>J</sub> =125°C	14.1	
			T <sub>J</sub> =150°C	16.5	
R <sub>θJC</sub>	Diode Thermal Resistance: Junction-To-Case (per leg)			0.166	°C/W

### Diode-Chopper

#### Maximum Rated Values of Diode (T<sub>C</sub> = 25°C unless otherwise specified)

V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	V
I <sub>F</sub>	Diode Continuous Forward Current	300	A
I <sub>FM</sub>	Peak FWD Current Repetitive	600	A

#### Electrical Characteristics of Diode (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
V <sub>FM</sub>	Forward Voltage	I <sub>F</sub> =300A	T <sub>J</sub> =25°C	1.80		V
			T <sub>J</sub> =125°C	1.80		
			T <sub>J</sub> =150°C	1.80		
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =300A, -diF/dt =2010A/μs(T <sub>J</sub> =150°C), V <sub>R</sub> = 600V, V <sub>GE</sub> = -15V	T <sub>J</sub> =25°C	0.41		μs
			T <sub>J</sub> =125°C	0.60		
			T <sub>J</sub> =150°C	0.64		
I <sub>rr</sub>	Peak Reverse Recovery Current		T <sub>J</sub> =25°C		150	A
			T <sub>J</sub> =125°C		181	
			T <sub>J</sub> =150°C		191	
Q <sub>rr</sub>	Reverse Recovery Charge	T <sub>J</sub> =25°C		29.7	μC	
		T <sub>J</sub> =125°C		50.7		
		T <sub>J</sub> =150°C		57.8		

E <sub>rec</sub>	Reverse Recovery Energy	I <sub>F</sub> =300A, -di <sub>F</sub> /dt =2010A/μs(T <sub>J</sub> =150°C), V <sub>R</sub> = 600V, V <sub>GE</sub> = -15V	T <sub>J</sub> =25°C	12.9	mJ
			T <sub>J</sub> =125°C	22.0	
			T <sub>J</sub> =150°C	25.4	
R <sub>θJC</sub>	Diode Thermal Resistance: Junction-To-Case (per leg)			0.134	°C/W

## Module

Symbol	Description		Min	Typ	Max	Unit
V <sub>iso</sub>	Isolation Voltage (All Terminals Shorted)	f = 50Hz, 1minute	2500			V
T <sub>J</sub>	Maximum Junction Temperature				175	°C
T <sub>JOP</sub>	Maximum Operating Junction Temperature Range		-40		+150	°C
T <sub>stg</sub>	Storage Temperature		-40		+125	°C
CTI	Comparative Tracking Index		200			
R <sub>θCS</sub>	Case-To-Sink Thermally (Conductive Grease Applied)			0.03		°C/W
T	Power Terminals Screw:M6		3.0		5.0	N·m
T	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			300		g

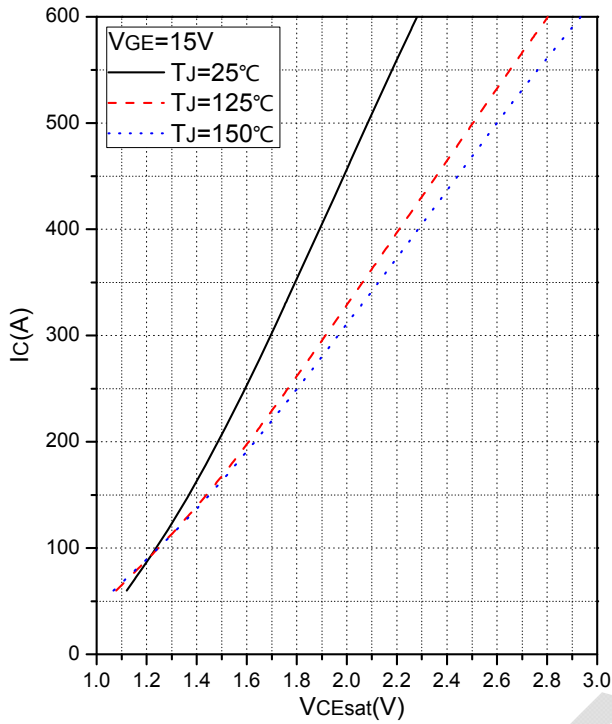


Fig.1 Typical Saturation Voltage Characteristics

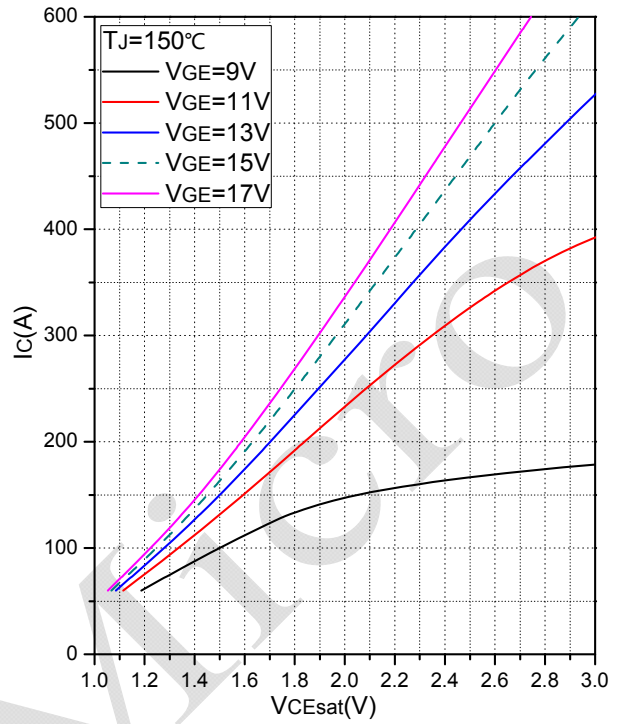


Fig.2 Typical Output Characteristics

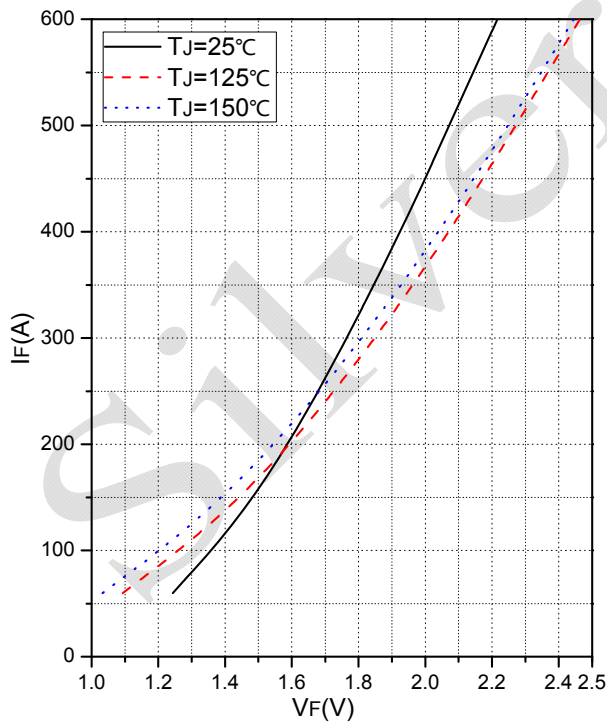


Fig.3 Forward Characteristics of Chopper Diode

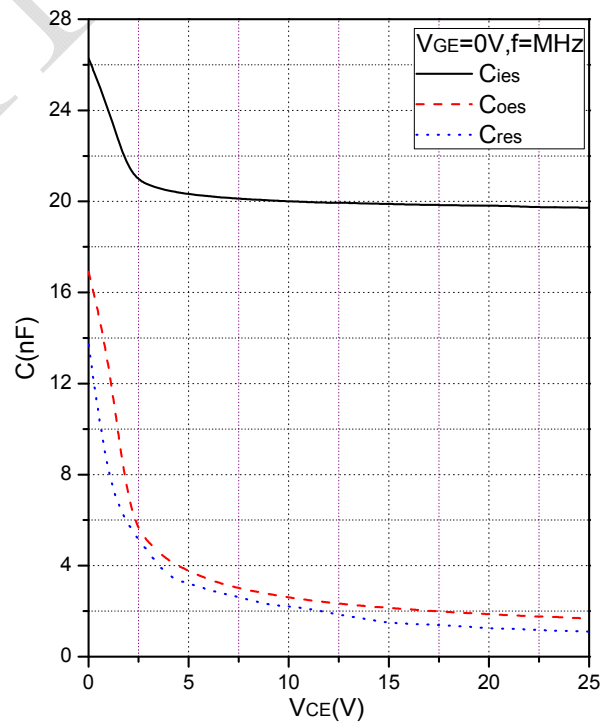


Fig.4 Capacitance Characteristics

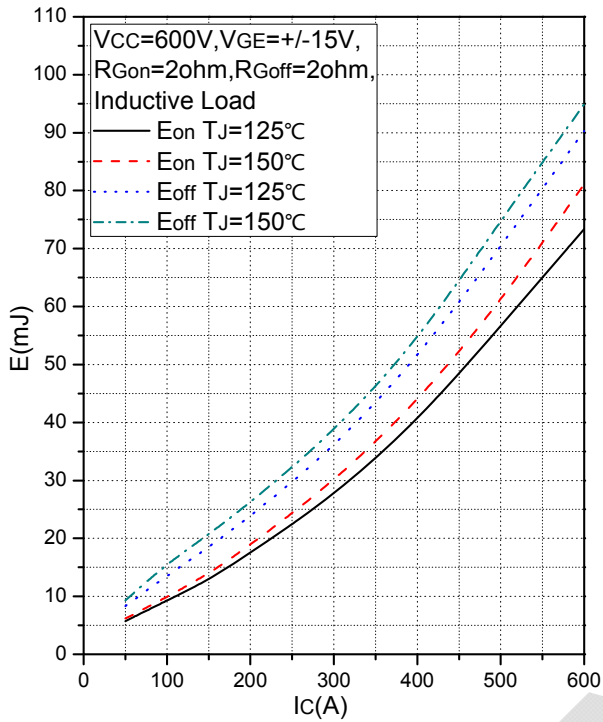


Fig.5 Typical Switching Loss vs. Collector Current

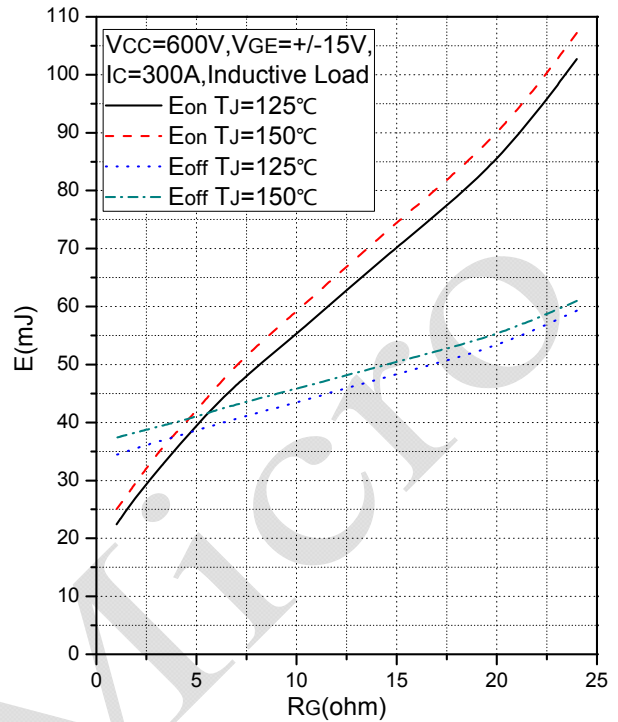


Fig.6 Typical Switching Loss vs. Gate Resistance

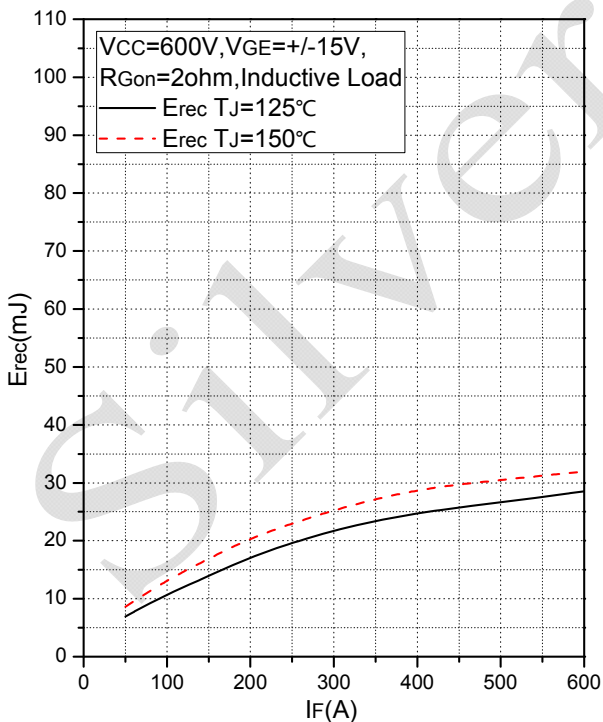


Fig.7 Typical Switching Loss vs. Forward Current

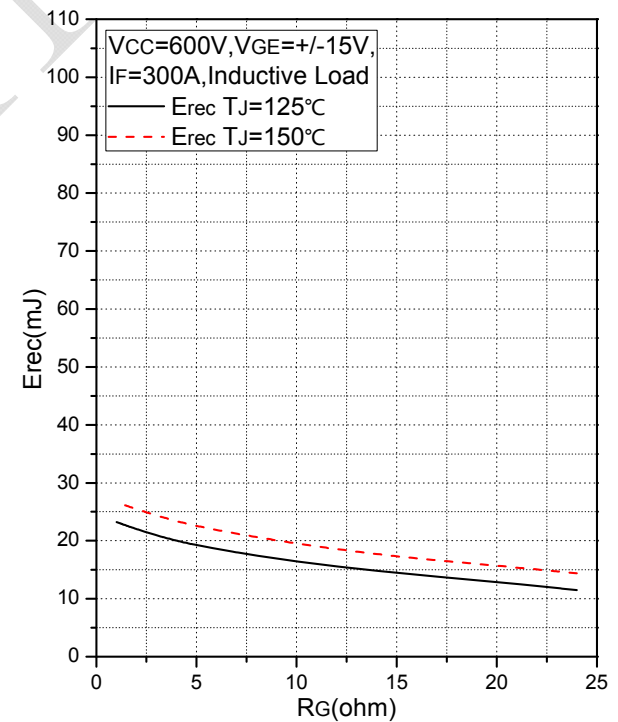


Fig.8 Typical Switching Loss vs. Gate Resistance

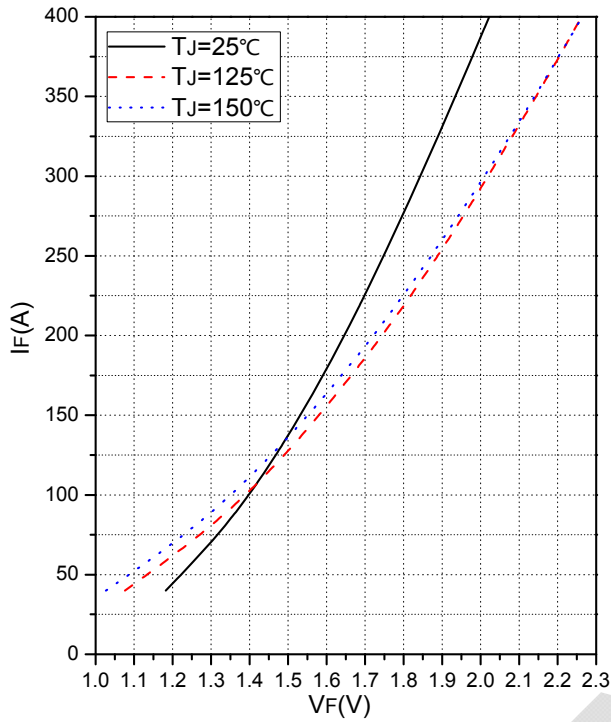


Fig.9 Forward Characteristics of Reverse Diode

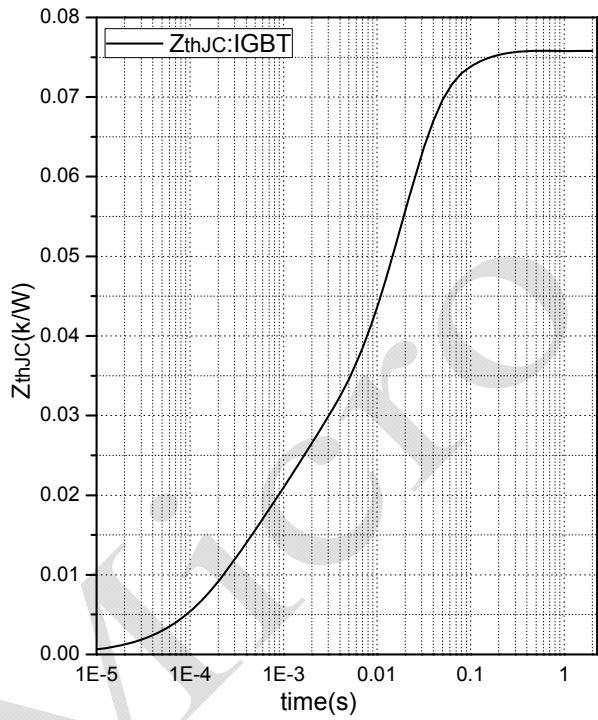


Fig.10 Transient Thermal Impedance (IGBT)

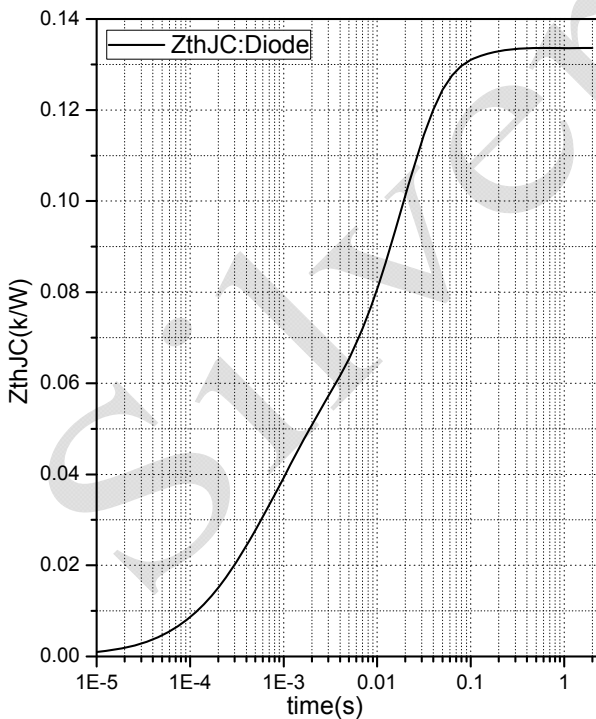


Fig.11 Transient Thermal Impedance (Brake-Chopper Diode)

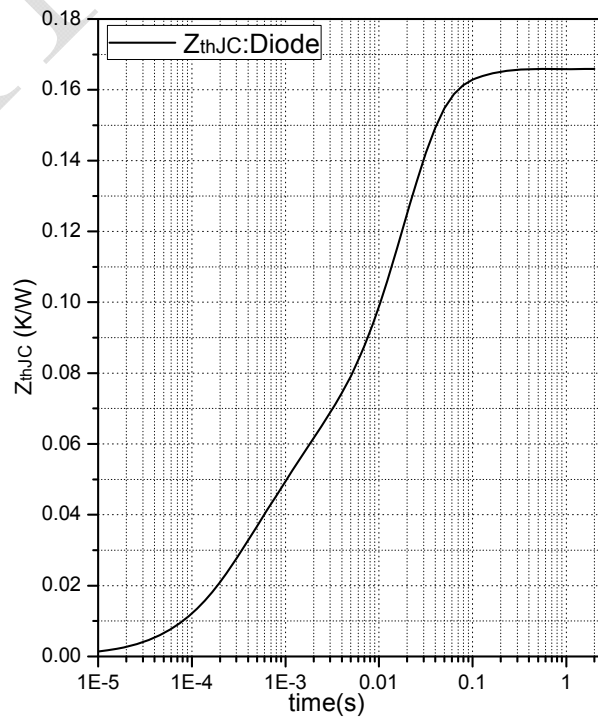


Fig.12 Transient Thermal Impedance (Reverse Diode)



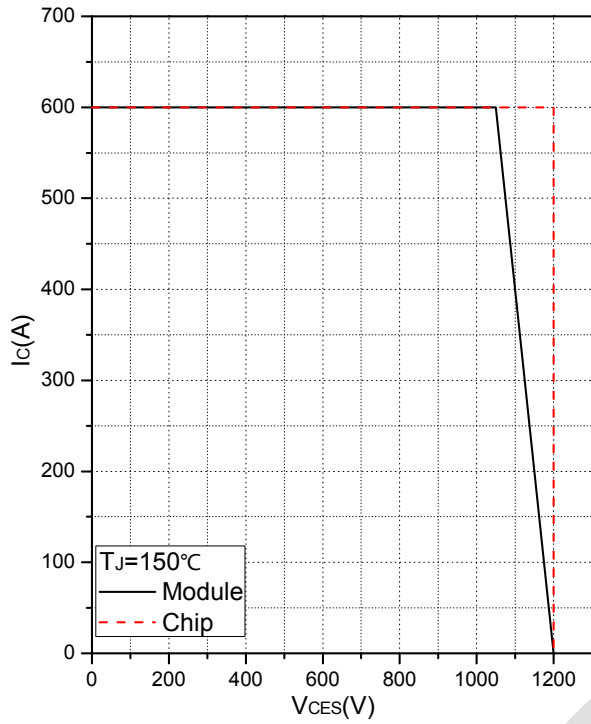
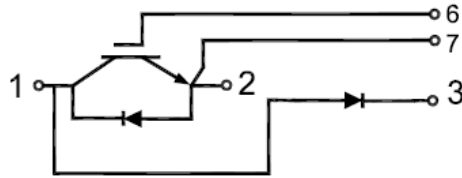
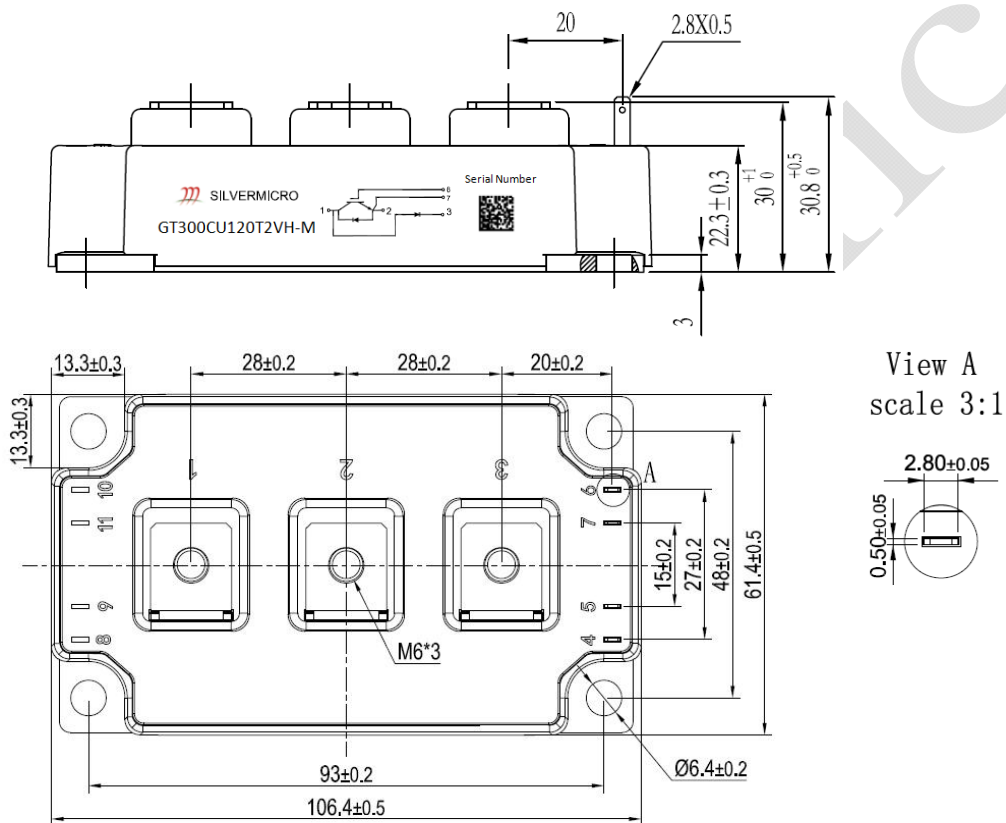


Fig.13 Reverse Bias Safe Operation Area (RBSOA)

### Internal Circuit



### Package Outline (Unit: mm):





Date	Revision	Notes
12/30/2019	01	Initial release

## Announcement

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